Effect of Irradiation Damage on Fission Product Transport: FY2017 Progress

AGR TRISO Fuels Program Review July 18-19, 2017

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Outline

- Background and Objectives
- FY2017 work scope
- Neutron Damage: Defect density and irradiation temperature
- Neutron Induced Phase Transformations
- HRTEM structures of Particle AGR1-411-030
- Conclusions
- Recommendations: Future Work
- Acknowledgements





Background: Transport Mechanisms

- Complex interactive mechanism likely:
 - neutron damage,
 - grain boundary characteristics,
 - chemical interaction with Pd, and
 - vapor transport



[I. J. van Rooyen, H. Nabielek, J. H Neethling, M. Kania and D.A. Petti, PROGRESS IN SOLVING THE ELUSIVE AG TRANSPORT MECHANISM IN TRISO COATED PARTICLES: "WHAT IS NEW?" Paper 31261, Proceedings of the 2014 International HTR-2014 Conference of High Temperature Reactors, Weihai, China, 2014]



Neutron Damage (FY2017)

Work focus on neutron damage and its effects on:

- Fuel performance
- Fission product distribution
- Bulk and grain boundary fission product transport mechanisms.
- This work will narrow the gap in understanding the effect of neutron irradiation on fission product transport in the intact SiC layer of TRISO-coated particles.



Neutron Damage: Scope and Matrix

- Correlate neutron-induced microstructural
 - defect density,
 - volume fraction, and
 - morphology with neutron irradiation parameters (i.e., neutron fluence and temperature)
- Analyze the defect density and distribution in the vicinity of fission product precipitates



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Neutron Damage: Defect Density and Irradiation Temperature

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Neutron Damage: Defect density and irradiation temperature

* Volume fraction and densities of **voids** can give insights to the irradiation temperature



Neutron irradiation induced voids are non-uniformly distributed. Voids are aligned along stacking faults.



Voids have tetragonal shape

Effect of fluence on size and density

 $1.9 \ {
m x} \ 10^{25} \ {
m n/m^{2,}}$



 $9.6 \times 10^{25} \text{ n/m}^{2.5}$

[S. Kondo, Y. Katoh, and L. L. Snead, Unidirectional formation of tetrahedral voids in irradiated silicon carbide, Appl. Phys. Lett. 93, 163110 (2008)]

S Kondo et al, JNM 382 (208) 160 -169]

AGR2-223-RS06, Lamella 9 (SiC/OPyC)

Estimated Temperature > 1400 °C



Neutron Damage: Defect density and irradiation temperature



Below 800 °C: Black spots dominant defects

800 -1150 °C : some black spots, small loops, Frank Loops

1300-1460 °C : irradiation fluence affects defect density and size, larger Frank loops (>20 nm in radius).



Defect Size, Morphology and Concentration differences??



- Preferential formations of cavities at stacking faults were confirmed above 1300 °C
- Small cavities were dispersed with low number density at 1130 °C [S Kondo et al, JNM 382 (208) 160 -169]



Distribution of voids around nanoscale precipitates



Yellow arrows indicates α -SiC or Pd precipitates



AGR1-632-034



Tetragonal shaped voids around nanoscale precipitates



Yellow arrows indicates α -SiC or Pd precipitates

AGR1-523-SP01



Neutron Induced Phase Transformations



Unirradiated SiC (Variant 3 Fuel Compact T0650)



- β-SiC
- Stacking Faults
- No α -SiC region
- No apparent frank loops









For the consistency of the study, all of the TEM were carried out along <001> zone axis of b-SiC matrix



Blue arrows: structures at the end of Frank loops along {111} planes Red arrow: structure with one of its edge at a stacking fault

Frank loop: are linear defects, introduced due to neutron irradiation here *Stacking fault:* are planar defects, often present in close packed materials such as SiC





Only Si and C

Si, C and Pd



Also described by: [Chad M. Parish, Takaaki Koyanagi, Sosuke Kondo

&Yutai Katoh, Irradiation-induced β to α SiC transformation at low temperature]

Tan TY et al On the diamond cubic to

Ute Kaiser, Nanocrystal formation in hexagonal SiC after Ge+ ion implantation, Journal of electron microscopy 50(3): 251-263 (2001)

hexagonal phase transformation in SiC Phil. Mag. A 44: 127-140, 1981

High Resolution (HR)TEM: for structural analysis



 $\{111\}_{\beta} || \{0006\}_{\alpha}$

 α -SiC precipitate appear to nucleate at the edge of a Frank loop

Some of the structures were confirmed to be irradiation induced low temperature α -SiC

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Case 2



Surprisingly, $\{002\}_{\beta} || \{0006\}_{\alpha}$

 $\alpha\text{-SiC}$ lies on a stacking fault

 $\alpha\mbox{-SiC}$ appears have multiple orientation with $\beta\mbox{-SiC}$

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High Resolution (HR)TEM of Pd rich precipitates



L1₂ structure of precipitate corresponds to Pd₃Si stoichiometry *Pd rich precipitates were confirmed to be Pd₃Si, based on their stoichiometry



Intragranular presence of Pd in SiC



- STEM image showing the different crystallography and mass contrast within the hexagonal structure
- It has been reported that reaction of Pd with α -SiC is easier than β -SiC, hence
- Pd₃Si adopts the morphology of parent surrogate a-SiC: Metamorphosis

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Intragranular presence of Pd in SiC





Particle AGR1-411-030



Intragranular Presence of Pd in SiC: Particle AGR1-411-030





[E J Olivier, J H Neethling, I J van Rooyen, Cs-corrected STEM and EDS Investigation of Pd and Ag transport along SiC grain boundaries and dislocations, Baotou China, 4th SiC workshop]

University



Intragranular Presence of Pd in SiC: Inclusions with void-like nature



[E J Olivier, J H Neethling, I J van Rooyen, Cs-corrected STEM and EDS Investigation of Pd and Ag transport along SiC grain boundaries and dislocations, Baotou China, 4th SiC workshop]

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Intragranular Presence of Ag in SiC: Particle AGR1-411-030



[E J Olivier, J H Neethling, I J van Rooyen, Cs-corrected STEM and EDS Investigation of Pd and Ag transport along SiC grain boundaries and dislocations, Baotou China, 4th SiC workshop]





Conclusions

- Neutron induced phase transformation of SiC:
 - α-SiC regions found at Frank loops and Stacking Faults of both AGR-1 and AGR-2 particles
 - α -SiC regions appears to have multiple orientations with β -SiC matrix
- No α-SiC regions and Frank loops identified in unirradiated AGR-1 and AGR-2 particles
- Some Transformed regions contain Pd
 - Although Pd is found as the main intragranular fission product, the possibility of Pd assisted transport of other elements cannot be ruled out.
 - Pd rich precipitates confirmed to corresponds to Pd₃Si



Recommendations: Future Work

- Expand the neutron damage work currently performed by correlating neutron-induced microstructural findings:
 - defect density,
 - volume fraction, and
 - morphology

with neutron irradiation parameters (i.e., neutron fluence and temperature (based on microstructural features of this study)

- Analyze the defect density and distribution in the vicinity of fission product precipitates
- Integrate PED, neutron damage, chemical composition and structural information for fission product mechanisms





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Questions??

What now?? Isabella van Rooyen Isabella.vanrooyen@inl.gov

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Technique Acronyms

Acronyms	Description
APT	Atom Probe Tomography
EDS	Energy Dispersive Spectroscopy
EBSD	Electron Back Scattered Diffraction
EELS	Electron Energy Loss Spectroscopy
EFTEM	Energy Filtered TEM
EPMA	Electron Probe Micro-Analysis
FIB	Focused Ion Beam
HRTEM	High Resolution Transmission Electron Microscopy
SAD	Selected Area Diffraction
SEM	Scanning Electron Microscope
STEM	Scanning Transmission Electron Microscopy
TEM	Transmission Electron Microscope
t-EBSD	Transmission-EBSD
TKD	Transmission Kikuchi Diffraction
WDS	Wavelength Dispersive Spectroscopy



Sub nanometer inclusions and vacancies Sub nm inclusions

